# Dual General Purpose Transistor

The MBT3906DW1 device is a spin –off of our popular SOT–23/SOT–323 three –leaded device. It is designed for general purpose amplifier applications and is housed in the SOT –363 six–leaded surface mount package. By putting two discrete devices in one package, this device is ideal for low –power surface mount applications where board space is at a premium.

#### Features

- h<sub>FE</sub>, 100–300
- Low  $V_{CE(sat)}$ ,  $\leq 0.4 \text{ V}$
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- Available in 8 mm, 7-inch/3,000 Unit Tape and Reel
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant\*

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V <sub>CEO</sub>	-40	Vdc
Collector – Base Voltage	V <sub>CBO</sub>	-40	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	-5.0	Vdc
Collector Current – Continuous	۱ <sub>C</sub>	-200	mAdc
Electrostatic Discharge	ESD	HBM Class 2 MM Class B	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Package Dissipation (Note 1) T <sub>A</sub> = 25°C	P <sub>D</sub>	150	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	833	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C

1. Device mounted on FR4 glass epoxy printed circuit board using the minimum recommended footprint.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

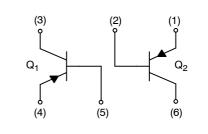


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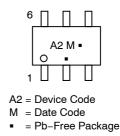
http://onsemi.com



SOT-363/SC-88 CASE 419B STYLE 1



#### MARKING DIAGRAM



(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MBT3906DW1T1G	SOT-363 (Pb-Free)	3,000 / Tape & Reel
MBT3906DW1T2G	SOT-363 (Pb-Free)	3,000 / Tape & Reel
SMBT3906DW1T1G	SOT-363 (Pb-Free)	3,000 / Tape & Reel

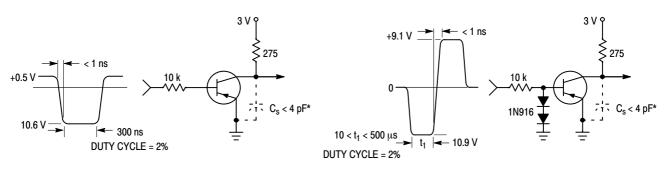
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Мах	Unit		
OFF CHARACTERISTICS	· · ·		•			
Collector - Emitter Breakdown Voltage (Note 2)	V <sub>(BR)CEO</sub>	-40	-	Vdc		
Collector – Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-40	-	Vdc		
Emitter – Base Breakdown Voltage	V <sub>(BR)EBO</sub>	-5.0	-	Vdc		
Base Cutoff Current	I <sub>BL</sub>	_	-50	nAdc		
Collector Cutoff Current	I <sub>CEX</sub>	_	-50	nAdc		
ON CHARACTERISTICS (Note 2)				•		
$ \begin{array}{l} \text{DC Current Gain} \\ (I_{C} = -0.1 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) \\ (I_{C} = -1.0 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) \\ (I_{C} = -10 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) \\ (I_{C} = -50 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) \\ (I_{C} = -100 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) \end{array} $	h <sub>FE</sub>	60 80 100 60 30	- - 300 - -	_		
Collector – Emitter Saturation Voltage ( $I_C = -10 \text{ mAdc}, I_B = -1.0 \text{ mAdc}$ ) ( $I_C = -50 \text{ mAdc}, I_B = -5.0 \text{ mAdc}$ )	V <sub>CE(sat)</sub>	-	-0.25 -0.4	Vdc		
Base – Emitter Saturation Voltage ( $I_C = -10 \text{ mAdc}, I_B = -1.0 \text{ mAdc}$ ) ( $I_C = -50 \text{ mAdc}, I_B = -5.0 \text{ mAdc}$ )	V <sub>BE(sat)</sub>	-0.65 -	-0.85 -0.95	Vdc		
SMALL-SIGNAL CHARACTERISTICS						
Current – Gain – Bandwidth Product	f <sub>T</sub>	250	-	MHz		
Output Capacitance	C <sub>obo</sub>	-	4.5	pF		
Input Capacitance	C <sub>ibo</sub>	-	10.0	pF		
Input Impedance $(V_{CE} = -10 \text{ Vdc}, I_C = -1.0 \text{ mAdc}, f = 1.0 \text{ kHz})$	h <sub>ie</sub>	2.0	12	kΩ		
Voltage Feedback Ratio ( $V_{CE} = -10$ Vdc, $I_C = -1.0$ mAdc, f = 1.0 kHz)	h <sub>re</sub>	0.1	10	X 10 <sup>-2</sup>		
Small – Signal Current Gain (V <sub>CE</sub> = –10 Vdc, I <sub>C</sub> = –1.0 mAdc, f = 1.0 kHz)	h <sub>fe</sub>	100	400	-		
Output Admittance $(V_{CE} = -10 \text{ Vdc}, I_C = -1.0 \text{ mAdc}, f = 1.0 \text{ kHz})$	h <sub>oe</sub>	3.0	60	μmhos		
Noise Figure (V <sub>CE</sub> = –5.0 Vdc, I <sub>C</sub> = –100 $\mu$ Adc, R <sub>S</sub> = 1.0 k $\Omega$ , f = 1.0 kHz)	NF	_	4.0	dB		
SWITCHING CHARACTERISTICS			•			
Delay Time (V <sub>CC</sub> = -3.0 Vdc, V <sub>BE</sub> = 0.5 Vdc)	t <sub>d</sub>	-	35			
Bise Time $(l_0 = -10 \text{ mAde } l_{0,1} = -10 \text{ mAde})$	+		35	ns ns		

Rise Time $(I_{C} = -10 \text{ mAdc}, I_{B1} = -1.0 \text{ mAdc})$		t <sub>r</sub>	-	35	ns
Storage Time	$(V_{CC} = -3.0 \text{ Vdc}, I_{C} = -10 \text{ mAdc})$	ts	-	225	20
Fall Time	(I <sub>B1</sub> = I <sub>B2</sub> = -1.0 mAdc)	t <sub>f</sub>	-	75	ns

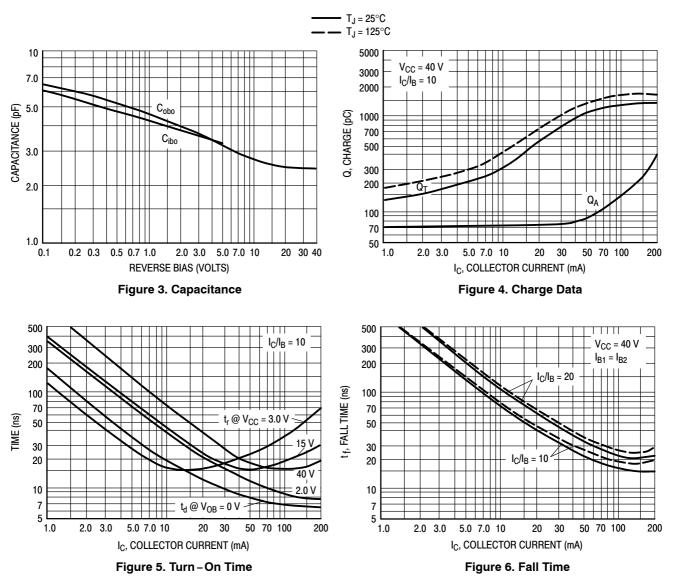
2. Pulse Test: Pulse Width  $\leq$  300  $\mu s;$  Duty Cycle  $\leq$  2.0%.



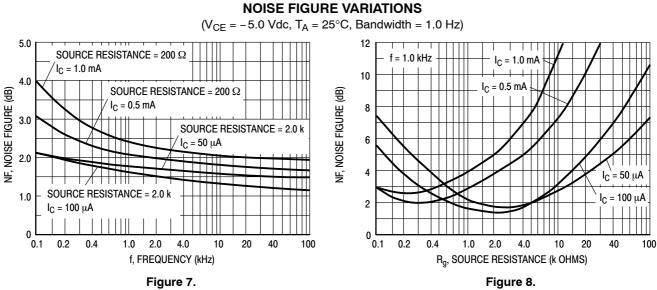
\* Total shunt capacitance of test jig and connectors

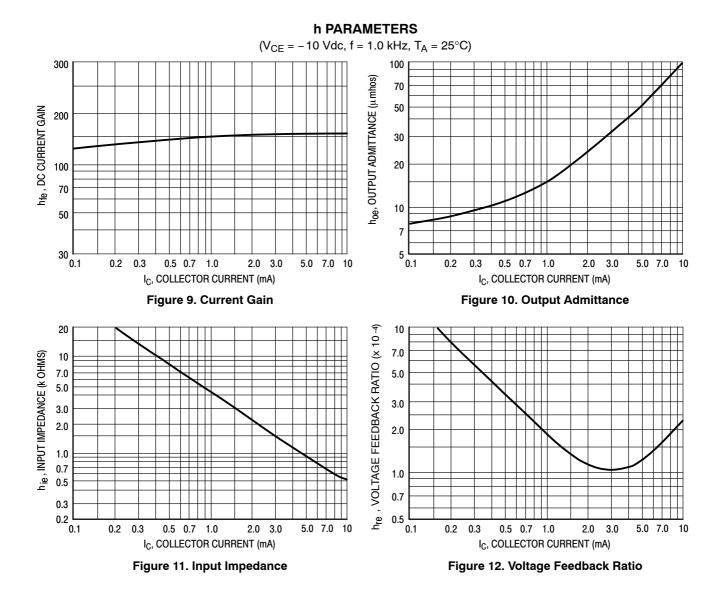
Figure 1. Delay and Rise Time Equivalent Test Circuit

Figure 2. Storage and Fall Time Equivalent Test Circuit



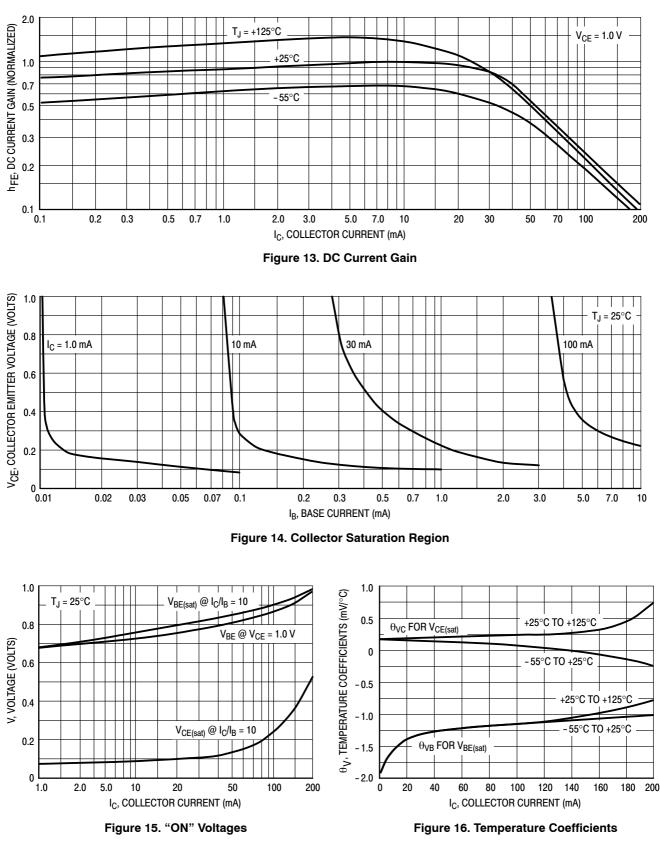
## **TYPICAL TRANSIENT CHARACTERISTICS**





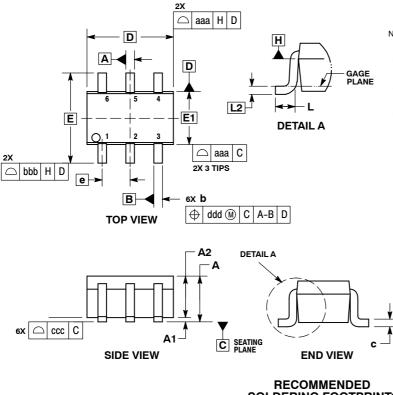
TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

#### **TYPICAL STATIC CHARACTERISTICS**



#### PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363 CASE 419B-02 **ISSUE Y** 



NOTES DIMENSIONING AND TOLERANCING PER ASME Y14.5M. 1994.

- 1. 2. CONTROLLING DIMENSION: MILLIMETERS.
- З.
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRU-SIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF 4
- THE PLASTIC BODY AND DATUM H. 5
- DATUMS A AND B ARE DETERMINED AT DATUM H. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP. 6.
- 7 DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDI-TION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α			1.10			0.043
A1	0.00		0.10	0.000		0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
Е	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
е	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
CCC	0.10			0.004		
ddd	0.10			0.004		

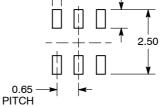
STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3 COLLECTOR 1



5. BASE 1



## **SOLDERING FOOTPRINT\*** <sup>6X</sup> 0.30 -0.66



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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